Unit: mm

TOSHIBA Transistor Silicon NPN Epitaxial Planar Type

# MT6L58AE

#### VHF~UHF Band Low Noise Amplifier Applications

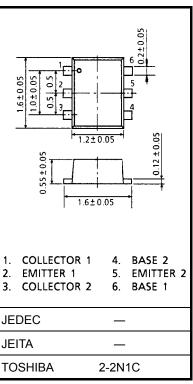
• Two devices are built in to the super-thin and extreme super mini (6 pins) package: ES6

#### **Mounted Devices**

	Q1: SSM (TESM)	Q2: SSM (TESM)
Three-pins (SSM/TESM) mold products are corresponded.	MT3S06S	MT3S03AS
	(MT3S06T)	(MT3S03AT)

### Absolute Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Q1	Q2	Unit
Collector-base voltage	$V_{CBO}$	10	10	V
Collector-emitter voltage	$V_{CEO}$	5	5	V
Emitter-base voltage	$V_{EBO}$	1.5	2	٧
Collector current	Ic	15	40	mA
Base current	ΙΒ	7	10	mA
Collector power dissipation	P <sub>C</sub> (Note 1)	100		mW
Junction temperature	Tj	125		°C
Storage temperature range	T <sub>stg</sub>	-55~125		°C



Weight: 0.003 g (typ.)

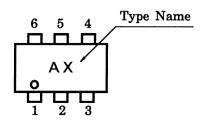
Note: Using continuously under heavy loads (e.g. the application of

high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

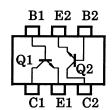
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: Total power dissipation of Q1 and Q2.

#### Marking



#### Pin Assignment (top view)



# **Electrical Characteristics Q1 (Ta = 25°C)**

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit	
Collector cut-off current	I <sub>CBO</sub>	$V_{CB} = 5 \text{ V}, I_{E} = 0$	_	_	0.1	μА	
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> = 1 V, I <sub>C</sub> = 0	_	_	1	μА	
DC current gain	h <sub>FE</sub>	V <sub>CE</sub> = 1 V, I <sub>C</sub> = 5 mA	70	_	140		
Transition frequency	f <sub>T</sub>	$V_{CE} = 3 \text{ V}, I_{C} = 5 \text{ mA}$	7	10	_	GHz	
Insertion gain	S <sub>21e</sub>   <sup>2</sup> (1)	$V_{CE} = 1 \text{ V}, I_{C} = 5 \text{ mA}, f = 2 \text{ GHz}$	_	7.5	_	dB	
	S <sub>21e</sub>   <sup>2</sup> (2)	$V_{CE} = 3 \text{ V}, I_{C} = 7 \text{ mA}, f = 2 \text{ GHz}$	4.5	8	_	uБ	
Noise figure	NF (1)	$V_{CE} = 1 \text{ V}, I_{C} = 3 \text{ mA}, f = 2 \text{ GHz}$	_	1.7	3	— dB	
	NF (2)	$V_{CE} = 3 \text{ V}, I_{C} = 3 \text{ mA}, f = 2 \text{ GHz}$	_	1.6	3		
Reverse transfer capacitance	C <sub>re</sub>	$V_{CB} = 1 \text{ V}, I_E = 0, f = 1 \text{ MHz}$ (Note 2)	_	0.35	0.75	pF	

Note 2:  $C_{re}$  is measured by 3 terminal method with capacitance bridge.

### **Electrical Characteristics Q2 (Ta = 25°C)**

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit	
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> = 5 V, I <sub>E</sub> = 0	_	_	0.1	μА	
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> = 1 V, I <sub>C</sub> = 0	_	_	1	μА	
DC current gain	h <sub>FE</sub>	V <sub>CE</sub> = 1 V, I <sub>C</sub> = 5 mA	80	_	160		
Transition frequency	f <sub>T</sub> (1)	V <sub>CE</sub> = 1 V, I <sub>C</sub> = 5 mA	5	7	_	GHz	
	f <sub>T</sub> (2)	V <sub>CE</sub> = 3 V, I <sub>C</sub> = 10 mA	7	10	_		
Insertion gain	S <sub>21e</sub>   <sup>2</sup> (1)	V <sub>CE</sub> = 1 V, I <sub>C</sub> = 5 mA, f = 2 GHz	_	5	_	dB	
	S <sub>21e</sub>   <sup>2</sup> (2)	$V_{CE} = 3 \text{ V}, I_{C} = 20 \text{ mA}, f = 2 \text{ GHz}$	3	6.5	_		
Noise figure	NF (1)	V <sub>CE</sub> = 1 V, I <sub>C</sub> = 5 mA, f = 2 GHz	_	1.7	3	dB	
	NF (2)	V <sub>CE</sub> = 3 V, I <sub>C</sub> = 7 mA, f = 2 GHz	_	1.4	2.2		
Reverse transfer capacitance	C <sub>re</sub>	$V_{CB} = 1 \text{ V}, I_E = 0, f = 1 \text{ MHz}$ (Note 2)	_	0.8	1.15	pF	

Note 2: Cre is measured by 3 terminal method with capacitance bridge.

## **Handling Precaution**

When handling individual devices (which are not yet mounted on a circuit board), be sure that the environment is protected against electrostatic electricity. Operators should wear anti-static clothing, and containers and other objects that come into direct contact with devices should be made of anti-static materials.

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20070701-EN GENERAL

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